## **Supporting Information**

## Molecular Glass Resists based on 9,9'-Spirobifluorene Derivatives: Pendant Effect and Comprehensive Evaluation in EUV Lithography

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\*Jinping Chen: chenjp@mail.ipc.ac.cn; \*Yi Li: yili@mail.ipc.ac.cn; \*Guoqiang Yang: gqyang@iccas.ac.cn Synthesis of MGs. MS spectra, TG and DSC curves, Schematic deprotection reactions, and SEM images.



Scheme S1. Synthesis of the MGs.



Figure S1. MS spectra of SP derivatives



Figure S2. TG and DSC curves of SP-AD and SP-BU



**Figure S3.** SEM images of the lines (up) and corresponding cross-section (bottom) patterns at exposure time of 16s and 30s, thickness of the dense lines is about 80nm and 67nm.



Figure S4. Schematic deprotection for the SP-BOC, SP-BU and SP-AD resist



Figure S5. SEM image of line-space patterns (top view) for SP-AD resist



Figure S6. SEM image of fractured film of SP-AD